### Silicon N-Channel MOS FET

# HITACHI

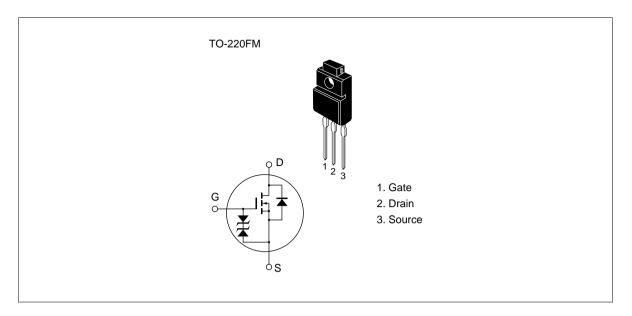
#### Application

High speed power switching

#### Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
  - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

#### Outline





#### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	100	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	10	A
Drain peak current	I D(pulse) * 1	40	А
Body to drain diode reverse drain current	I <sub>DR</sub>	10	А
Channel dissipation	Pch*2	25	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	٥C

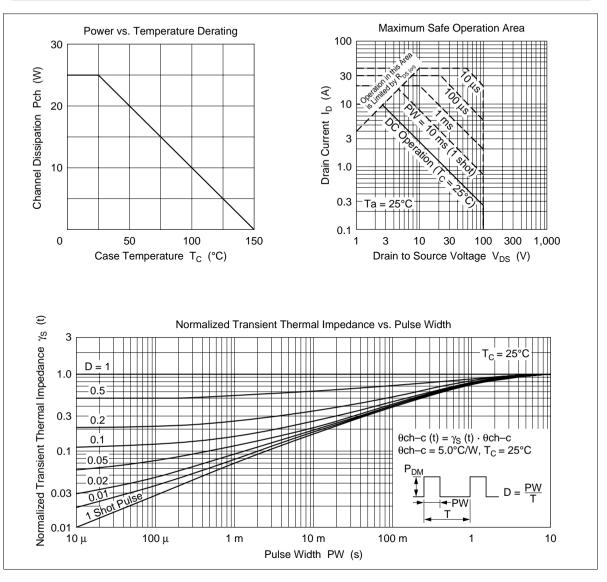
Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at  $T_c = 25^{\circ}C$ 

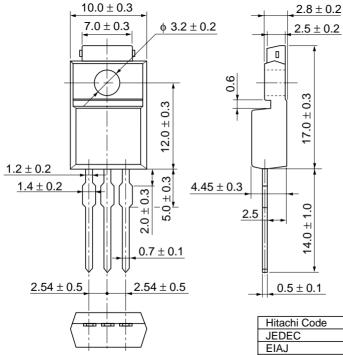
#### **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	100	_	_	V	$I_{\rm D} = 10$ mA, $V_{\rm GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_{g} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>		—	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, \text{ V}_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		—	250	μΑ	$V_{\rm DS} = 80 \ V, \ V_{\rm GS} = 0$
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	1.0	—	2.0	V	$I_{\rm D} = 1 \text{ mA}, V_{\rm DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{\text{DS(on)}}$	_	0.20	0.25	Ω	$I_{\rm D} = 5$ A, $V_{\rm GS} = 10$ V * <sup>1</sup>
		_	0.25	0.35	Ω	$I_{\rm D} = 5$ A, $V_{\rm GS} = 4$ V * <sup>1</sup>
Forward transfer admittance	yfs	4.5	7.0		S	$I_{\rm D} = 5 \text{ A}, V_{\rm DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss		525		pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss		205		pF	f = 1 MHz
Reverse transfer capacitance	Crss		60	_	pF	
Turn-on delay time	t <sub>d(on)</sub>		5	—	ns	$I_{\rm D} = 5 \text{ A}, V_{\rm GS} = 10 \text{ V},$
Rise time	t,		50		ns	$R_{L} = 6 \Omega$
Turn-off delay time	t <sub>d(off)</sub>		170	—	ns	
Fall time	t <sub>f</sub>		75		ns	
Body to drain diode forward voltage	$V_{\text{DF}}$	_	1.2	_	V	$I_{F} = 10 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>	—	220	—	ns	$I_{\rm F} = 10 \text{ A}, V_{\rm GS} = 0, \\ di_{\rm F}/dt = 50 \text{ A}/\mu \text{s}$
Note: 1. Pulse test						

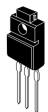
See characteristic curves of 2SK1300.



#### **HITACHI**



Unit: mm



Hitachi Code	TO-220FM
JEDEC	
EIAJ	Conforms
Weight (reference value)	1.8 g

#### Cautions

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